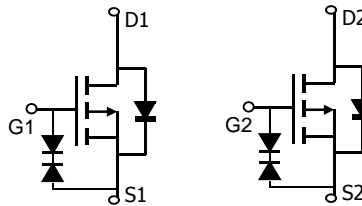
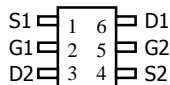


**AO7801**
**Dual P-Channel Enhancement Mode Field Effect Transistor**
**General Description**

The AO7801 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge, and operation with gate voltages as low as 1.8V, in the small SOT323 footprint. It can be used for a wide variety of applications, including load switching, low current inverters and low current DC-DC converters. It is ESD protected to 2KV HBM.

**Features**

$V_{DS}$  (V) = -20V  
 $I_D$  = -0.6A ( $V_{GS}$  = -4.5V)  
 $R_{DS(ON)} < 520m\Omega$  ( $V_{GS}$  = -4.5V)  
 $R_{DS(ON)} < 700m\Omega$  ( $V_{GS}$  = -2.5V)  
 $R_{DS(ON)} < 950m\Omega$  ( $V_{GS}$  = -1.8V)


**SC-70-6  
(SOT-323)  
Top View**

**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}$	-0.6
		$T_A=70^\circ\text{C}$	-0.48
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-3	A
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ\text{C}$	0.3
		$T_A=70^\circ\text{C}$	0.19
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10\text{s}$	360	415
Maximum Junction-to-Ambient <sup>A</sup>		Steady-State	400	460
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	300	350	$^\circ\text{C/W}$

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-20			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±10	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.5	-0.6	-0.9	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-3			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.6A T <sub>J</sub> =125°C		400 542	520 700	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.5A		540	700	mΩ
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-0.4A		700	950	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-0.6A		1.7		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-0.5A, V <sub>GS</sub> =0V		-0.86	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-0.4	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-10V, f=1MHz		114	140	pF
C <sub>oss</sub>	Output Capacitance		17		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance		14		pF	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		12	17	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.6A		1.44	1.8	nC
Q <sub>gs</sub>	Gate Source Charge		0.14		nC	
Q <sub>gd</sub>	Gate Drain Charge		0.35		nC	
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, R <sub>L</sub> =16.7Ω, R <sub>GEN</sub> =3Ω		6.5		ns
t <sub>r</sub>	Turn-On Rise Time		6.5		ns	
t <sub>D(off)</sub>	Turn-Off DelayTime		18.2		ns	
t <sub>f</sub>	Turn-Off Fall Time		5.5		ns	
t <sub>rr</sub>	Body Diode Reverse Recovery Time		I <sub>F</sub> =-0.6A, dI/dt=100A/μs		10	13
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-0.6A, dI/dt=100A/μs		3		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in <sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The SOA curve provides a single pulse rating.

Rev2: May 2012

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

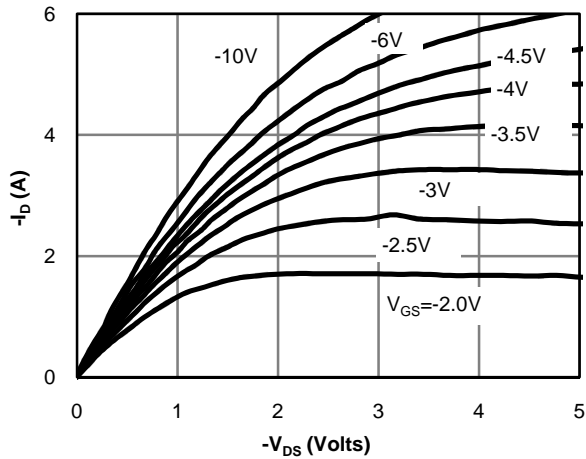


Fig 1: On-Region Characteristics

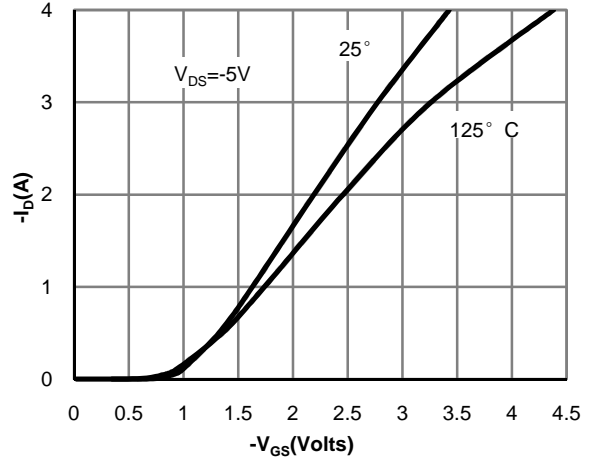


Figure 2: Transfer Characteristics

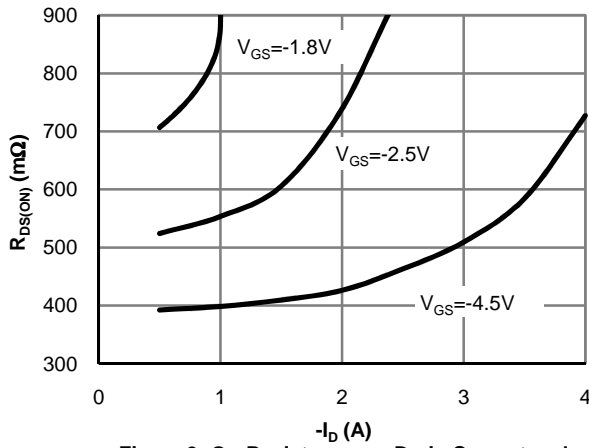


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

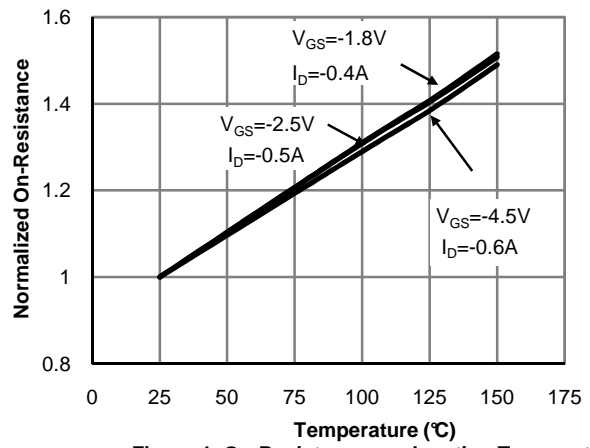


Figure 4: On-Resistance vs. Junction Temperature

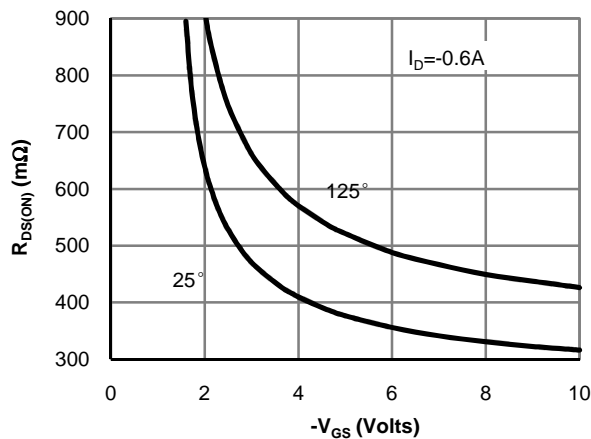


Figure 5: On-Resistance vs. Gate-Source Voltage

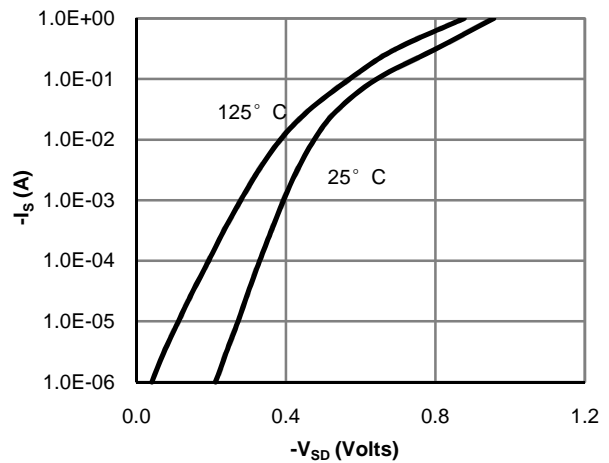


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

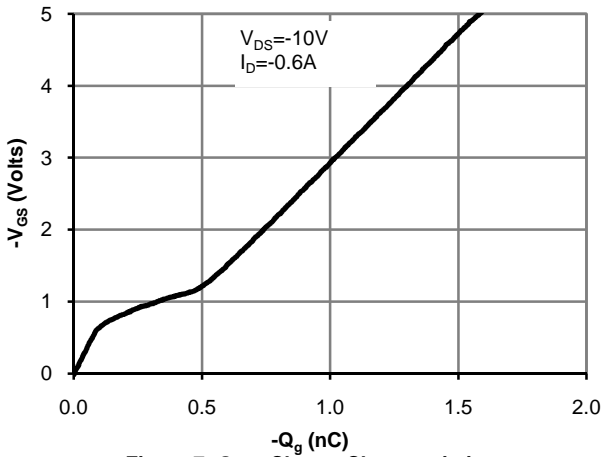


Figure 7: Gate-Charge Characteristics

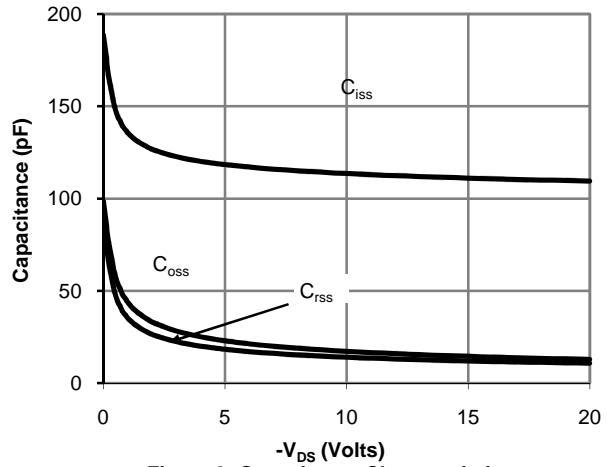


Figure 8: Capacitance Characteristics

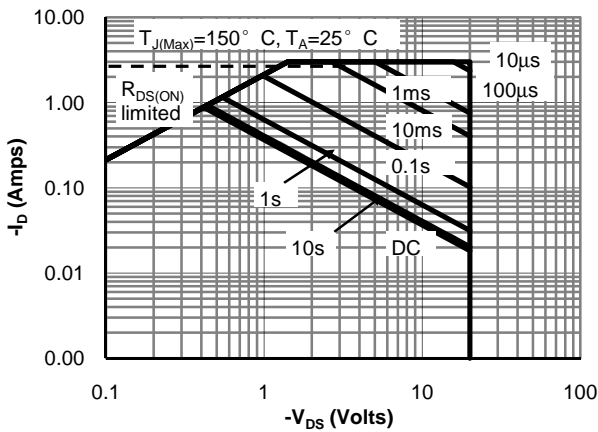


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

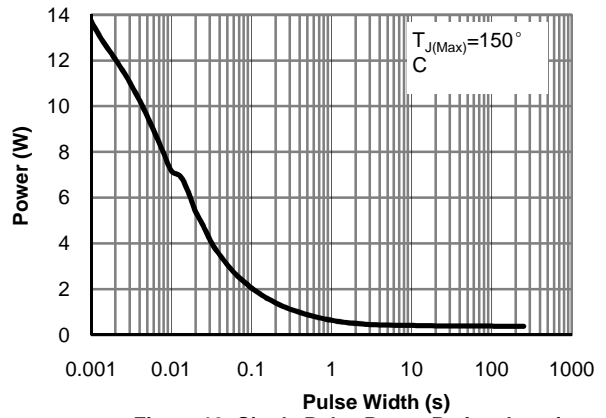


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

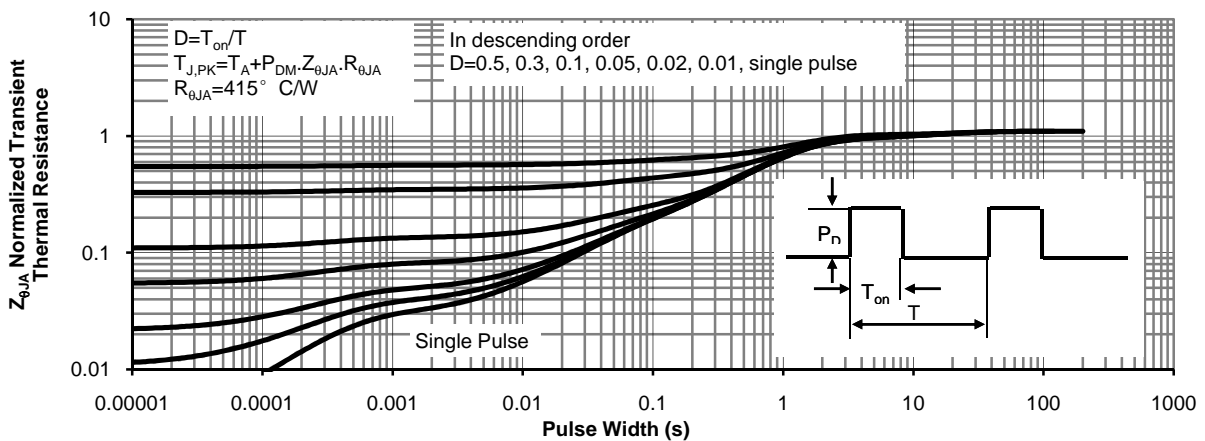


Figure 11: Normalized Maximum Transient Thermal Impedance